

# 4V Drive Nch MOSFET

## RSD080N06

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) 4V drive.
- 3) High power package(CPT3).

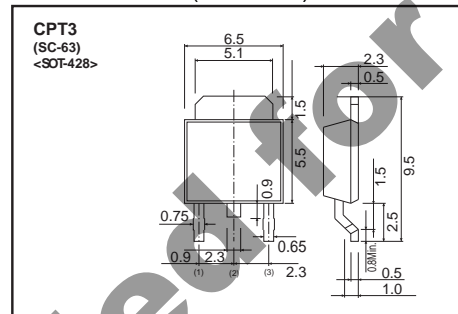
### ● Application

Switching

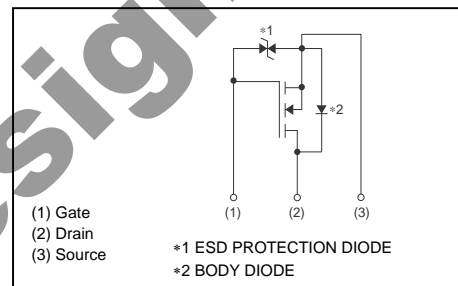
### ● Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	2500
RSD080N06		○

### ● Dimensions (Unit : mm)



### ● Inner circuit



### ● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-source voltage	$V_{DSS}$	60	V
Gate-source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	Continuous	$I_D$	$\pm 8$ A
	Pulsed	$I_{DP}$ *1	$\pm 16$ A
Source current (Body Diode)	Continuous	$I_S$	8 A
	Pulsed	$I_{SP}$ *1	16 A
Power dissipation	$P_D$ *2	15	W
Channel temperature	Tch	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$

\*2  $T_C = 25^\circ C$

### ● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th}(ch-c)^*$	8.33	°C / W

\*  $T_C = 25^\circ C$

## ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	$\pm 10$	$\mu A$	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu A$	$V_{DS}=60V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	1.0	-	2.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	57	80	m $\Omega$	$I_D=8A, V_{GS}=10V$
		-	70	98		$I_D=8A, V_{GS}=4.5V$
		-	78	109		$I_D=8A, V_{GS}=4.0V$
Forward transfer admittance	$ Y_{fs} ^*$	4.8	-	-	S	$V_{DS}=10V, I_D=8A$
Input capacitance	$C_{iss}$	-	380	-	pF	$V_{DS}=10V$
Output capacitance	$C_{oss}$	-	90	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	-	50	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	9	-	ns	$V_{DD}=30V, I_D=4A$
Rise time	$t_r^*$	-	13	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	30	-	ns	$R_L=7.5\Omega$
Fall time	$t_f^*$	-	10	-	ns	$R_G=10\Omega$
Total gate charge	$Q_g^*$	-	9.4	-	nC	$V_{DD}=30V, I_D=8A$
Gate-source charge	$Q_{gs}^*$	-	1.8	-	nC	$V_{GS}=10V$
Gate-drain charge	$Q_{gd}^*$	-	2.3	-	nC	

\*Pulsed

## ● Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^*$	-	-	1.5	V	$I_s=8A, V_{GS}=0V$

\*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics ( I )

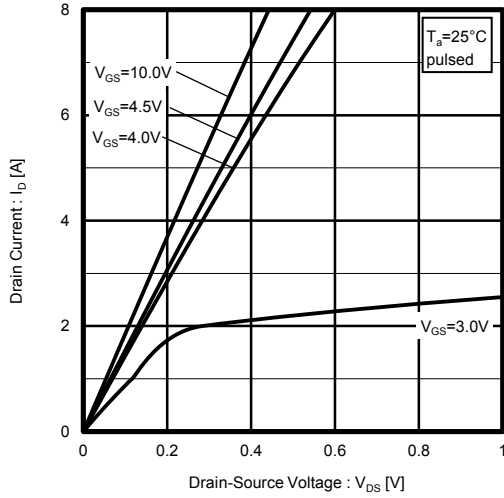


Fig.2 Typical Output Characteristics ( II )

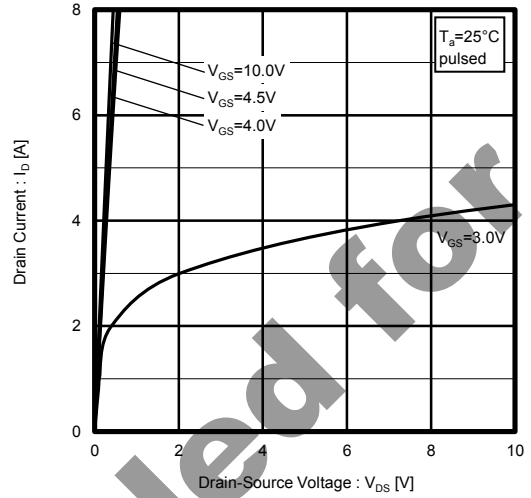


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

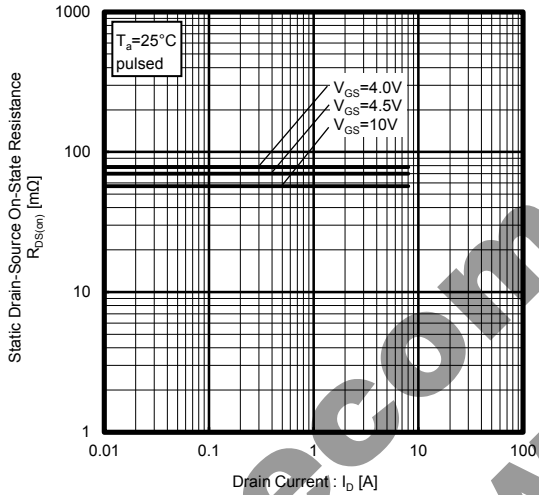


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

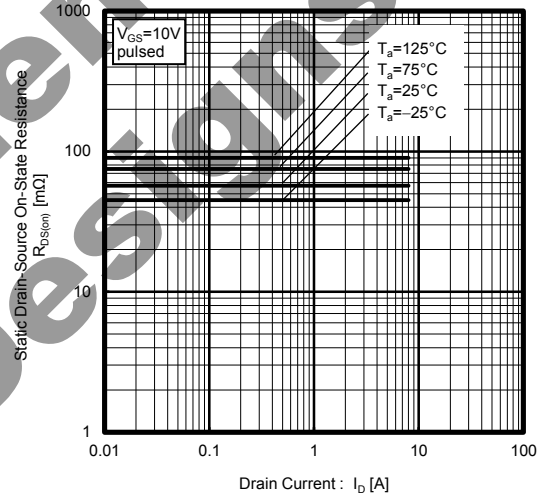


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

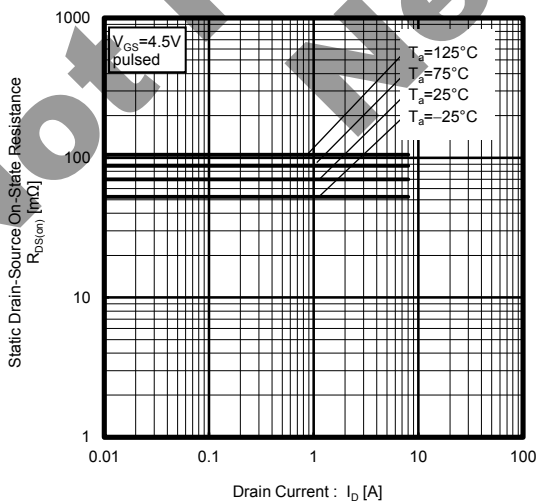


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

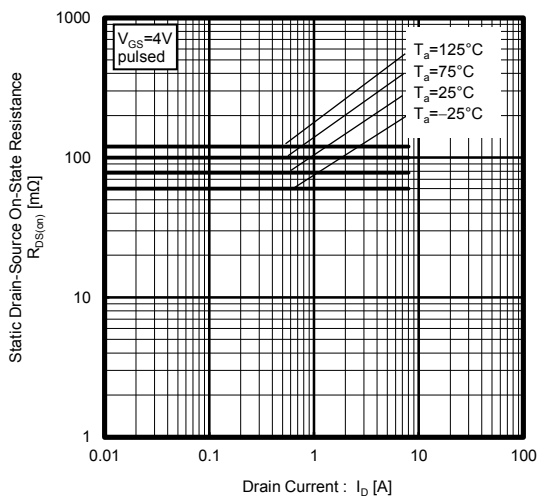


Fig.7 Forward Transfer Admittance vs. Drain Current

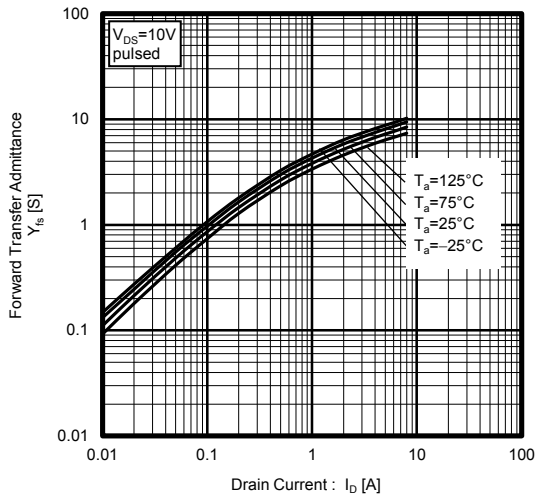


Fig.8 Typical Transfer Characteristics

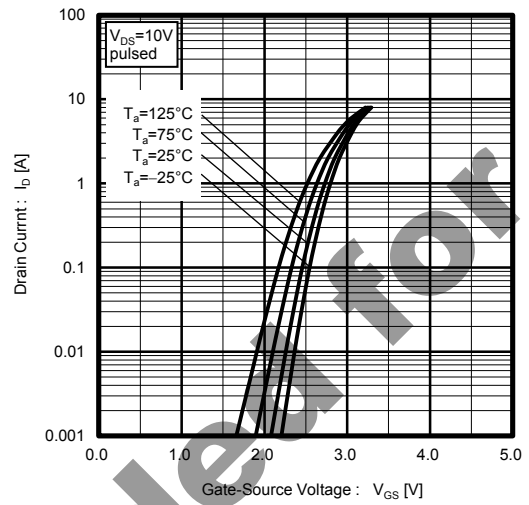


Fig.9 Source Current vs. Source-Drain Voltage

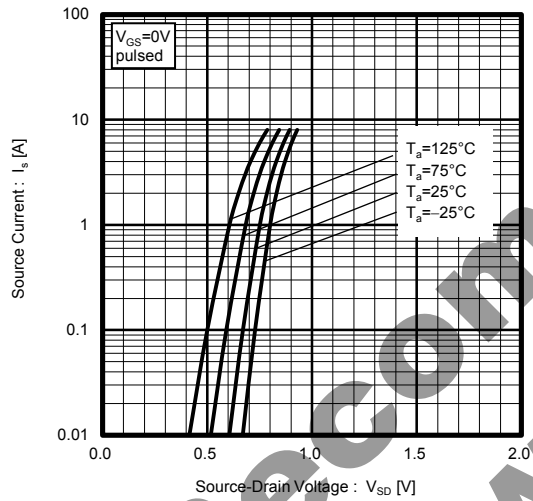


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

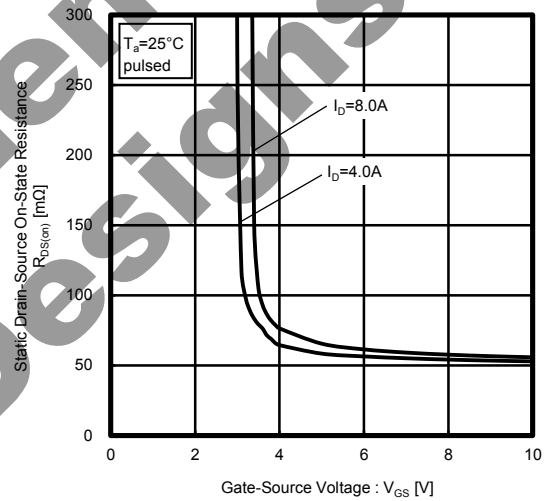


Fig.11 Switching Characteristics

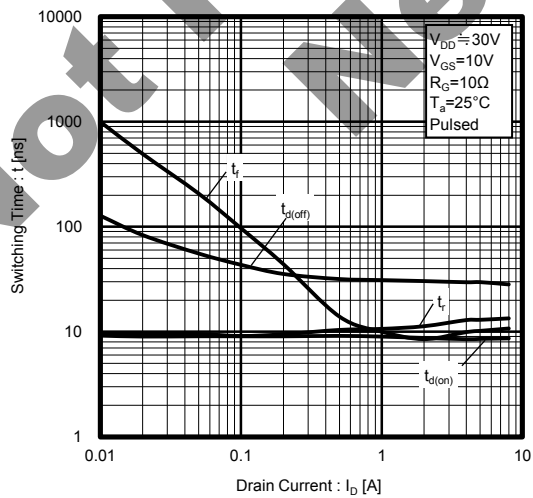


Fig.12 Dynamic Input Characteristics

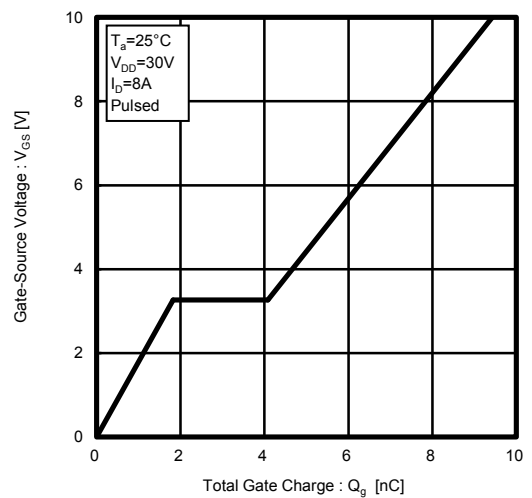


Fig.13 Typical Capacitance vs. Drain-Source Voltage

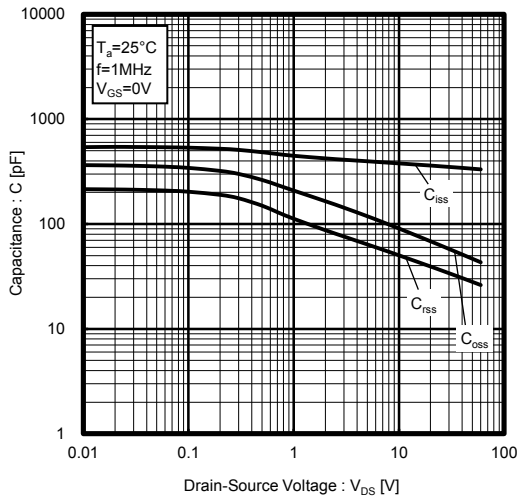


Fig.14 Maximum Safe Operating Area

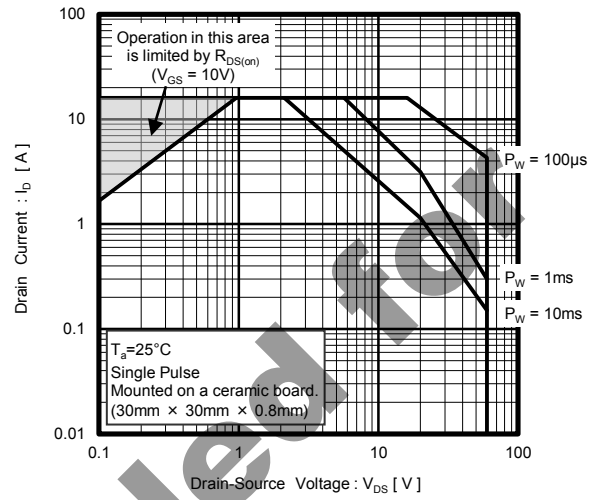
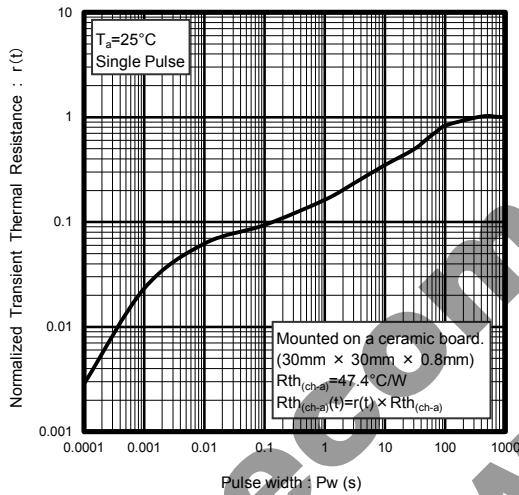


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



Not Recommended for New Designs

● Measurement circuits

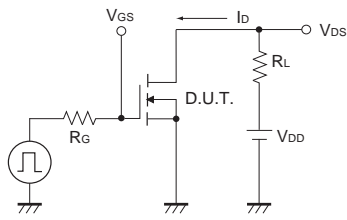


Fig.1-1 Switching Time Measurement Circuit

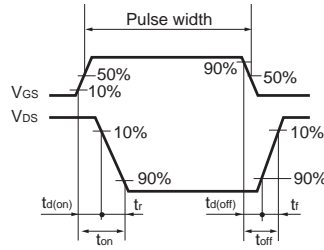


Fig.1-2 Switching Waveforms

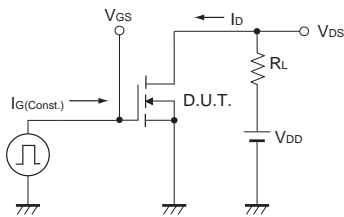


Fig.2-1 Gate Charge Measurement Circuit

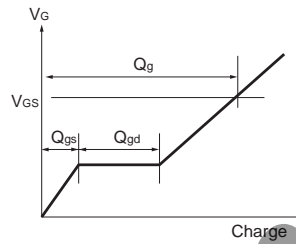


Fig.2-2 Gate Charge Waveform

Not Recommended for New Designs

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